



Atty. Docket No.
33035M0341

PATENT

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant(s): Kensaku Motoki, et al.

US Serial No.: 10/691,540

Group Art Unit: 1765

Filed: : October 24, 2003

Examiner: To Be Assigned

For : GaN Single Crystal Substrate and Method of Making the Same

SECOND INFORMATION DISCLOSURE STATEMENT

Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450


Sir:

Pursuant to the duty of disclosure under 37 C.F.R. 1.56, Applicants are enclosing an Information Disclosure Citation Form (PTO-1449) which lists the references cited in a Supplementary European Search Report issued for counterpart European Appln. No. EP 98 95 0452 dated February 19, 2004. In the Annex to the Search Report, U.S. Patent No. 5,970,314 is identified as a family member of EP 0 801 156. U.S. Patent Nos. 5,962,875 and 5,834,325 are identified as family members of EP 0 810 674. Accordingly, these three U.S. patents also are listed on the enclosed PTO-1449 form.

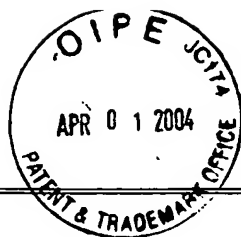
Applicants certify under 37 C.F.R. 1.97(e)(1) that all documents submitted herewith were first cited in a communication from a foreign patent office in a counterpart foreign application not more than three months prior to the filing of this Statement. Therefore, it is respectfully urged that no fees are required for the Examiner's consideration of the documents listed in this Information Disclosure Statement.

It is respectfully requested that the cited documents be considered by the Examiner in the above-identified patent application and that the cited documents be made officially of record therein. It is further requested that a listing of the same appear on the face of any patent which may issue from this application.

Respectfully submitted,
SMITH, GAMBRELL & RUSSELL, LLP

By: 
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Date: April 1, 2004



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| FORM PTO-1449 INFORMATION DISCLOSURE STATEMENT | ATTY. DOCKET 33035M0341 | SERIAL NO. 10/691,540 |
| | Applicant Kensaku Motoki, et al. | |
| | FILING DATE October 24, 2003 | GROUP ART UNIT 1765 |

U.S. PATENT DOCUMENTS

| *Examiner's Initials | | DOCUMENT NUMBER | DATE | NAME | CLASS | SUB-CLASS | FILING DATE, IF APPROPRIATE |
|----------------------|----|-----------------|----------|-----------------|-------|-----------|-----------------------------|
| | AA | 5,970,314 | 10/19/99 | Okahisa, et al. | | | |
| | AB | 5,962,875 | 10/5/99 | Motoki, et al. | | | |
| | AC | 5,834,325 | 11/10/98 | Motoki, et al. | | | |

FOREIGN PATENT DOCUMENTS

| *Examiner's Initials | | DOCUMENT NUMBER | DATE | COUNTRY | CLASS | SUB-CLASS | TRANSLATION YES NO | |
|----------------------|----|-----------------|----------|---------|-------|-----------|-----------------------|--|
| | AD | WO 96/41906 | 12/27/96 | PCT | | | | |
| | AE | EP 0 801 156 | 10/15/97 | EPO | | | | |
| | AF | EP 0 810 674 | 12/3/97 | EPO | | | | |

OTHER INFORMATION (Including Author, Title, Date, Pertinent Pages, Etc.)

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| | AG | Masaki Nagahara, et al., "Selective Growth of Cubic GaN in Small Areas on Patterned GaAs (100) Substrates by Metalorganic Vapor Phase Epitaxy", Japanese Journal of Applied Physics, Publication Office Japanese Journal of Applied Physics, Vol. 33, No. 1B, Part 1, (1994), pp. 694-697, XP000596419 |
| | AH | X. Li, et al., "Characteristics of GaN Stripes Grown by Selective-Area Metalorganic Chemical Vapor Deposition", Journal of Electronic Materials, Vol. 26, No. 3, (1996), pp. 306-310, XP009004611 |
| | AI | Database Inspec 'Online! Institute of Electrical Engineers, Stevenage, GB; Matsushima H. et al., "Sub-micron fine structure of GaN by metalorganic vapor phase epitaxy (MOVPE) selective area growth (SAG) and buried structure by epitaxial lateral overgrowth (ELO)", Database accession no. 6037425 XP-002268861 |
| | AJ | Database Inspec 'Online! Institute of Electrical Engineers, Stevenage, GB; Shibata T et al., "Hybride vapor-phase epitaxy growth of high-quality GaN bulk single crystal by epitaxial lateral overgrowth", Database accession no. 6037423 XP-002268862 |
| | AK | Database Inspec 'Online! Institute of Electrical Engineers, Stevenage, GB; Sasaoka C et al., "High-quality InGaN MQW on low-dislocation-density GaN substrate grown by hydride vapor-phase epitaxy", Database accession no. 6037422 XP-002268863 |

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| EXAMINER: | DATE CONSIDERED: |
| <p>*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.</p> | |